General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

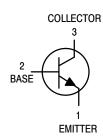
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

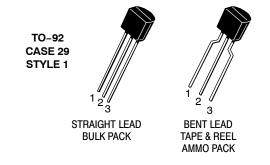
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



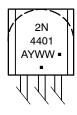
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



2N4401 = Device Code A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit	
OFF CHARACTERISTICS				•	•	•
Collector – Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)		V _{(BR)CEO}	40	-	Vdc	
Collector-Base Breakdown	Voltage	$(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V _{(BR)CBO}	60	-	Vdc
Emitter-Base Breakdown V	oltage	(I _E = 0.1 mAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current		(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{BEV}	-	0.1	μAdc
Collector Cutoff Current		(V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{CEX}	-	0.1	μAdc
ON CHARACTERISTICS (N	lote 1)					
DC Current Gain		$ \begin{array}{l} (I_{C}=0.1 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=500 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \end{array} $	h _{FE}	20 40 80 100 40	- - 300 -	-
Collector - Emitter Saturation	n Voltage	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{CE(sat)}	- -	0.4 0.75	Vdc
Base - Emitter Saturation Vo	ltage	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{BE(sat)}	0.75 -	0.95 1.2	Vdc
SMALL-SIGNAL CHARAC	TERISTICS					
Current-Gain - Bandwidth Product (I _C = 20 mAdc, V _{CE} = 10 Vc		C = 20 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	250	_	MHz
Collector-Base Capacitance)	(V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	-	6.5	pF
Emitter-Base Capacitance		(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{eb}	-	30	pF
Input Impedance	($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{ie}	1.0	15	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	40	500	-	
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h _{oe}	1.0	30	μmhos	
SWITCHING CHARACTER	ISTICS					
Delay Time (V _{CC} = 30 Vdc, V _{BE} = 2.0 Vdc,		t _d	_	15	ns	
Rise Time	I _C = 150 mAdc, I _{B1} = 15 mAdc)		t _r	-	20	ns
Storage Time	Storage Time $(V_{CC} = 30 \text{ Vdc}, I_C = 150 \text{ mAdc},$		t _s	-	225	ns
Fall Time $I_{B1} = I_{B2} = 15 \text{ mAdc}$		Adc)	t _f	_	30	ns

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]	
2N4401	TO-92	5000 Units / Bulk	
2N4401G	TO-92 (Pb-Free)	5000 Units / Bulk	
2N4401RLRA	TO-92	2000 / Tape & Reel	
2N4401RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
2N4401RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	
2N4401RLRP	TO-92	2000 / Tape & Ammo Box	
2N4401RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

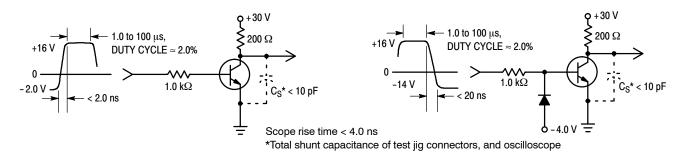


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS

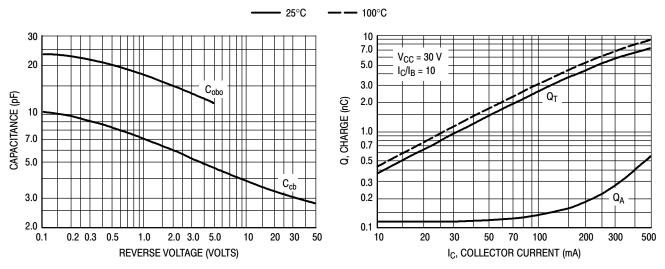


Figure 3. Capacitances

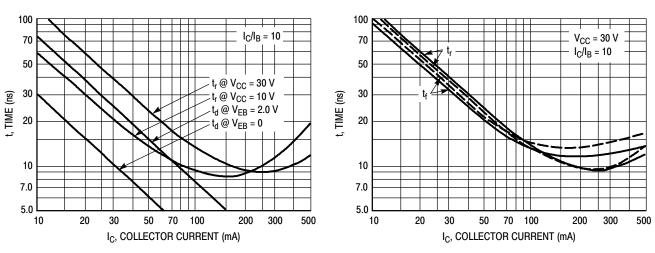
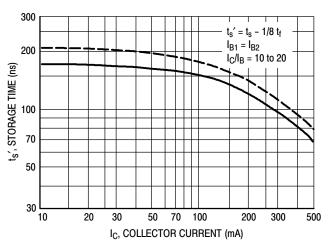


Figure 5. Turn-On Time

Figure 6. Rise and Fall Times

Figure 4. Charge Data



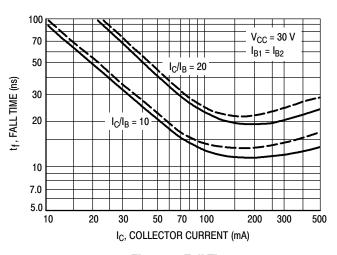
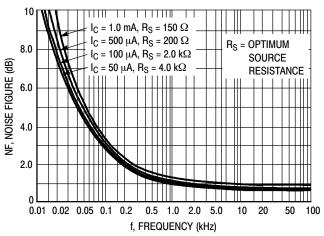


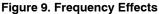
Figure 7. Storage Time

Figure 8. Fall Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz





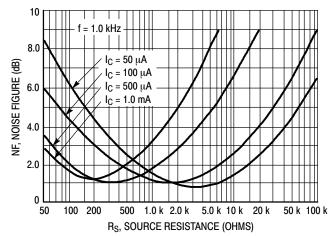


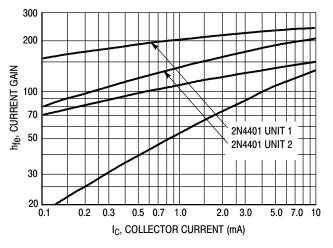
Figure 10. Source Resistance Effects

h PARAMETERS

 V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were

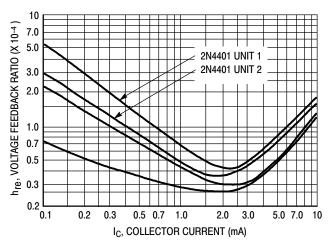
selected from the 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.



50 k 2N4401 UNIT 1 2N4401 UNIT 2 h_{ie}, INPUT IMPEDANCE (OHMS) 20 k 10 k 5.0 k 2.0 k 1.0 k 500 0.2 0.5 0.7 1.0 2.0 7.0 10 IC, COLLECTOR CURRENT (mA)

Figure 11. Current Gain

Figure 12. Input Impedance



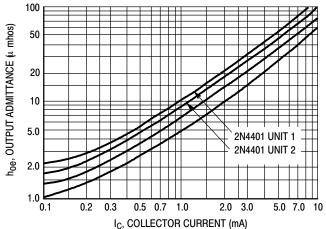


Figure 13. Voltage Feedback Ratio

Figure 14. Output Admittance

STATIC CHARACTERISTICS

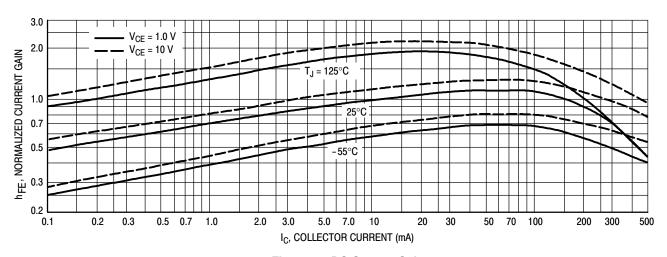


Figure 15. DC Current Gain

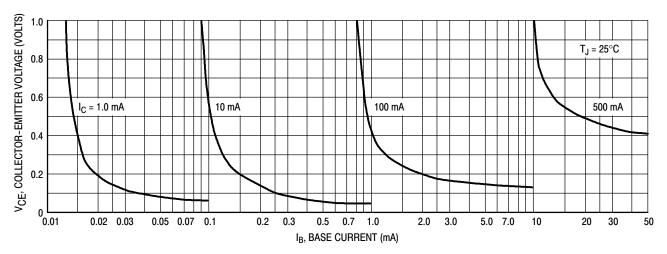


Figure 16. Collector Saturation Region

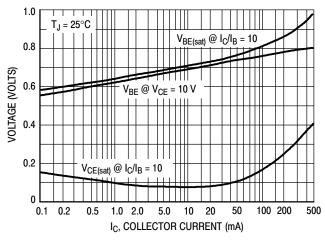


Figure 17. "On" Voltages

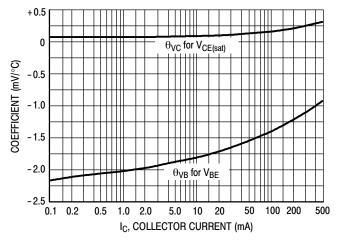
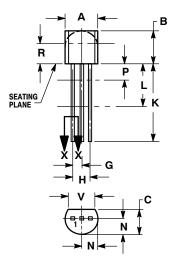


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

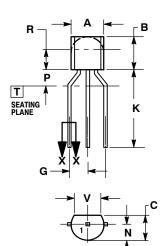


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100	-	2.54
R	0.115		2.93	
V	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION:
- MILLIMETERS
- DIMENSION R IS UNCONTROLLED.

 LEAD DIMENSION IS UNCONTROLLED IN
- P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93	-	
V	3 43		

PIN 1. EMITTER

BASE

COLLECTOR

ON Semiconductor and 👊 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, as patent rights of the rights of others. SCILLC products are not designed, interflaced, or administed to these as components in systems interflaced to support or surgical implant into the body, or of their applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Email: orderlit@onsemi.com

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your loca Sales Representative